

2SA699

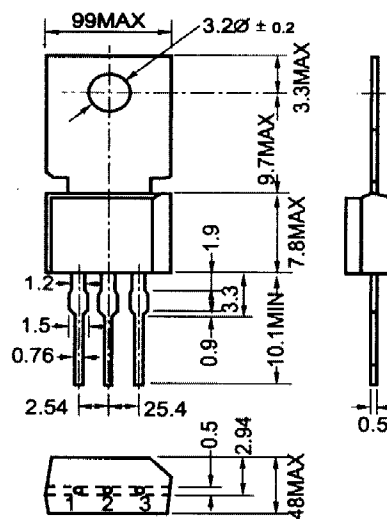
Silicon PNP Transistors

◆ Features

- With TO-202 package
- Complement to type: 2SC1226

◆ Absolute Maximum Ratings $T_c=25^\circ\text{C}$

SYMBOL	PARAMETER	RATING	UNIT
V_{CBO}	Collector to base voltage	40	V
V_{CEO}	Collector to emitter voltage	32	V
V_{EBO}	Emitter to base voltage	5.0	V
I_B	Base current		
I_C	Collector current	2	A
P_C	Collector power dissipation	10	W
T_J	Junction temperature	150	°C
T_{stg}	Storage temperature	-55~150	°C



TO-202

◆ Electrical Characteristics $T_c=25^\circ\text{C}$

SYMBOL	PARAMETER	CONDITIONS	MIN	TYPE	MAX	UNIT
I_{CBO}	Collector-base cut-off current	$V_{CB}=20V; I_E=0$			1	μA
I_{EBO}	Emitter-base cut-off current	$V_{EB}=5V; I_C=0$			100	μA
I_{CEO}	Collector-emitter cut-off current	$V_{CE}=12V; I_E=0$			100	μA
V_{CBO}	Collector-base breakdown voltage	$I_C=1\text{mA}; I_E=0$	40			V
V_{CEO}	Collector-emitter voltage	$I_C=10\text{mA}; I_B=0$	32			V
V_{EBO}	Emitter-base breakdown voltage					
$V_{CE(sat-1)}$	Collector-emitter saturation voltages	$I_C=1.5A; I_B=0.15A$			1.0	V
$V_{CE(sat-2)}$	Collector-emitter saturation voltages					
h_{FE-1}	Forward current transfer ratio	$I_C=1A; V_{CE}=5V$	50		220	
h_{FE-2}	Forward current transfer ratio					
$V_{BE(sat)1}$	Base-emitter saturation voltages	$I_C=2A; I_B=0.2A$			1.5	V
$V_{BE(sat)2}$	Base-emitter saturation voltages					
$V_{BE(sat)3}$	Base-emitter saturation voltages					
f_T	Transition frequency at $f=1\text{MHz}$	$I_C=0.5A; V_{CE}=5V$		150		MHz

Hfe Rank

P	Q	R
50-100	80-160	100-220

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